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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/026,019	12/20/2001	Ralph H. Johnson	15436.436.3	6105
22913 WORKMAN N	12/20/2001 Ralph H. Johnson 0 09/04/2007 DEGGER 1 TEMPLE TE TOWER	EXAMINER		
60 EAST SOU	TH TEMPLE		NGUYEN,	DUNG T
	12/20/2001 7590 09/04/2007 IYDEGGER		ART UNIT	PAPER NUMBER
	,		2828	
			MAIL DATE	DELIVERY MODE
			09/04/2007	PAPER

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

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	Application No.	Applicant(s)	
Office Action Summers	10/026,019	JOHNSON, RALPH H.	
Office Action Summary	Examiner	Art Unit	
	Dung (Michael) T. Nguyen	2828	
The MAILING DATE of this communication Period for Reply	appears on the cover sheet with	the correspondence address	
A SHORTENED STATUTORY PERIOD FOR RE WHICHEVER IS LONGER, FROM THE MAILING - Extensions of time may be available under the provisions of 37 CFI after SIX (6) MONTHS from the mailing date of this communication - If NO period for reply is specified above, the maximum statutory pe - Failure to reply within the set or extended period for reply will, by st Any reply received by the Office later than three months after the mearned patent term adjustment. See 37 CFR 1.704(b).	G DATE OF THIS COMMUNICA' R 1.136(a). In no event, however, may a reply . riod will apply and will expire SIX (6) MONTHS atute, cause the application to become ABANI	TION. be timely filed from the mailing date of this communication. DONED (35 U.S.C. § 133).	
Status			
1) Responsive to communication(s) filed on 2	<u>0 June 2007</u> .		
	This action is non-final.		
3) Since this application is in condition for allocation accordance with the practice und		•	
Disposition of Claims	o. En parto dadyio, 1900 O.D. 1	1, 1100 0.0. 210.	
<u> </u>	Od interes were altered to the second		
4) Claim(s) 2,3,5-7,9,14-16,18,21-30,33 and 3		on.	
4a) Of the above claim(s) is/are with 5) ☑ Claim(s) 14,24-30 and 33 is/are allowed.	drawn from consideration.		
6) Claim(s) <u>14,24-30 and 33</u> is/are allowed.	tod		
7) Claim(s) <u>3,9,16,18 and 22</u> is/are objected to			
8) Claim(s) are subject to restriction an			
Application Papers	 		
<u> </u>	-i		
9) The specification is objected to by the Exam		the Éveriner	
10) The drawing(s) filed on is/are: a)			
Applicant may not request that any objection to Replacement drawing sheet(s) including the cor		• •	
11) The oath or declaration is objected to by the			
·	. Examiner. Note the attached O	mice Action of form F10-152.	
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for fore	eign priority under 35 U.S.C. § 11	9(a)-(d) or (f).	
a) ☐ All b) ☐ Some * c) ☐ None of:			
 Certified copies of the priority docum 	ents have been received.		
Certified copies of the priority docum	• • • • • • • • • • • • • • • • • • • •		
Copies of the certified copies of the p		ceived in this National Stage	
application from the International Bur	, , , , , , , , , , , , , , , , , , , ,		
* See the attached detailed Office action for a	list of the certified copies not rec	eived.	
Attachment(s)			
Notice of References Cited (PTO-892)	4) 🔲 Interview Sumi	mary (PTO-413)	
2) D Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/M	ail Date	
B) Information Disclosure Statement(s) (PTO/SB/08) Paper No(s)/Mail Date	5) ☐ Notice of Inforr 6) ☐ Other:	mal Patent Application	

Application/Control Number: 10/026,019

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OFFICE ACTION

The indicated allowed claims 21-23 are withdrawn due to the newly found prior art.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 2, 5-7, 15, 21, 23, and 34 are rejected under 35 U.S.C. 102(e) as being anticipated by Tsuda et al. (6399966).

Claims 21 and 23, Fig.6, Table 1, and col.11, l.21-22 disclose an active region 406 comprising at least one quantum well with a thickness comprised of InGaAsN and including A1GaAs barrier layers sandwiching said at least one quantum well; and confinement layers 404 & 409 sandwiching said active region.

Claims 5-7, 34, Fig.6, Table 1, and col.11, 1.21-22 disclose

an active region 406 further comprising at least one quantum well with a thickness and including barrier layers sandwiching said at least one quantum well, at least one of the quantum well and the barrier layers including nitrogen, wherein said at least one quantum well is further comprised of Sb;

upper and lower confinement layers 404 & 409 sandwiching said active region, wherein the barrier layers and/or the upper and lower confinement layers are comprised of material that

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reduces a level of non-confining valence band discontinuity in the quantum well due to the presence of nitrogen in the quantum well (since Table 1 shows the presence of nitrogen in the QW, it is understood that the barrier layers and/or the upper and lower confinement layers must be comprised of material that reduces a level of non-confining valence band discontinuity in the quantum well due to the presence of nitrogen in the quantum well. Otherwise, the laser device would not work properly); and

a flattening layer 405 interposed between the lower confinement layer and the at least one quantum well.

Claim 2, Table 1 shows GaAsN barrier layers.

Claim 15, Table 1 shows InGaAs barrier layers.

Allowable Subject Matter

Claims 3, 9, 16, 18, and 22 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Claims 14, 24-30, and 33 are allowed.

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Communication Information

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Dung (Michael) T Nguyen whose telephone number is (571) 272-1949. The examiner can normally be reached on 8:30 - 17:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Min Harvey can be reached on (571) 272-1835. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 306-3329.

Michael Dung Nguyen

Juny w

Primary Examiner

8/24/02